

# **TSM2311**

## 20V P-Channel MOSFET



**SOT-23** 

# 3 1 2

#### Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

#### PRODUCT SUMMARY

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
-20	55 @ V <sub>GS</sub> = -4.5V	-4.0	
	85 @ V <sub>GS</sub> = -2.5V	-2.5	

## **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

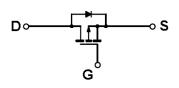
## **Application**

- Load Switch
- PA Switch

## **Ordering Information**

Part No.	Package	Packing
TSM2311CX RF	SOT-23	3Kpcs / 7" Reel

## **Block Diagram**



P-Channel MOSFET

## **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	-20	V	
Gate-Source Voltage		$V_{GS}$	±8	V	
Continuous Drain Current, V <sub>GS</sub> @4.5V.		I <sub>D</sub>	-4	А	
Pulsed Drain Current, V <sub>GS</sub> @4.5V		I <sub>DM</sub>	-20	А	
Continuous Source Current (Diode Con	duction) <sup>a,b</sup>	I <sub>S</sub>	-0.72	А	
Maximum Davier Discipation	Ta = 25°C	Б	0.9	W	
Maximum Power Dissipation	Ta = 75°C	P <sub>D</sub>	0.57		
Operating Junction Temperature		$T_J$	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C	

## **Thermal Performance**

Parameter	Symbol	Limit	Unit			
Lead Temperature (1/8" from case)	$T_L$	5	S			
Junction to Ambient Thermal Resistance (PCB mounted)	RO <sub>JA</sub>	250	°C/W			

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board,  $t \le 5$  sec.
- c. Surface Mounted on FR4 Board,



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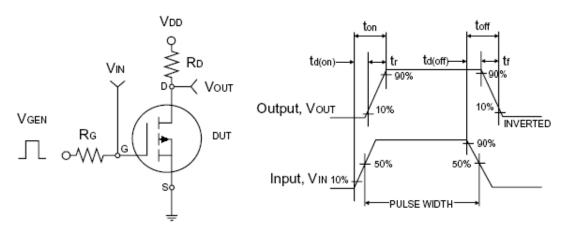


## **Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV <sub>DSS</sub>	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-0.45		-0.95	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$	I <sub>DSS</sub>			-1.0	μA
On-State Drain Current <sup>a</sup>	V <sub>DS</sub> ≥-10V, V <sub>GS</sub> = -5V	I <sub>D(ON)</sub>	-6			Α
Drain Cauras On Ctata Basistanas	$V_{GS} = -4.5V, I_{D} = -4A$	_		45	55	mΩ
Drain-Source On-State Resistance <sup>a</sup>	$V_{GS} = -2.5V, I_D = -2.5A$	$R_{DS(ON)}$		75	85	
Forward Transconductance <sup>a</sup>	$V_{DS} = -5V, I_{D} = -4A$	g <sub>fs</sub>		9		S
Diode Forward Voltage	$I_S = -0.75A$ , $V_{GS} = 0V$	$V_{SD}$		- 0.8	-1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	\/ - 6\/   - 4\	$Q_g$		6	9	
Gate-Source Charge	$V_{DS} = -6V, I_D = -4A,$ $V_{GS} = -4.5V$	$Q_gs$		1.4		nC
Gate-Drain Charge	V <sub>GS</sub> = -4.5 V	$Q_{gd}$		1.9		
Input Capacitance	\\ - 6\\ \\ - 0\\	C <sub>iss</sub>		640		
Output Capacitance	$V_{DS} = -6V, V_{GS} = 0V,$ f = 1.0MHz	$C_{oss}$		180		pF
Reverse Transfer Capacitance	1 - 1.0IVINZ	C <sub>rss</sub>		90		
Switching <sup>c</sup>						
Turn-On Delay Time	V - CV D - CO	t <sub>d(on)</sub>		22	35	
Turn-On Rise Time	$V_{DD} = -6V, R_L = 6\Omega,$ $I_D = -1A, V_{GEN} = -4.5V,$	t <sub>r</sub>		35	55	20
Turn-Off Delay Time		t <sub>d(off)</sub>		45	70	nS
Turn-Off Fall Time	$R_G = 6\Omega$	t <sub>f</sub>		25	50	

#### Notes:

- a. pulse test: PW  $\leq 300 \mu S$ , duty cycle  $\leq 2\%$  b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms

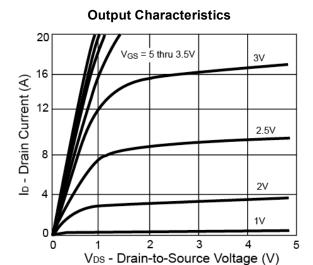




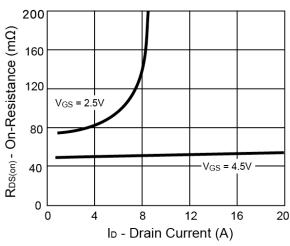




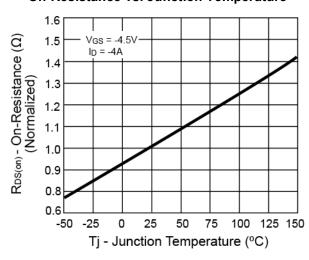
## Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



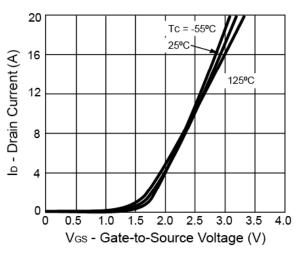
#### **On-Resistance vs. Drain Current**



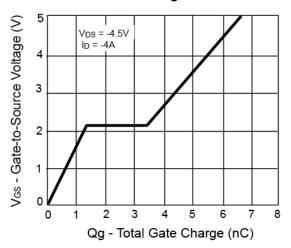
## **On-Resistance vs. Junction Temperature**



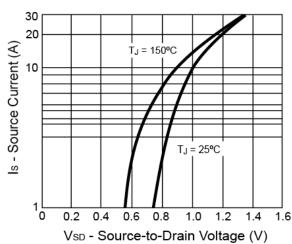
## **Transfer Characteristics**



## **Gate Charge**



## Source-Drain Diode Forward Voltage





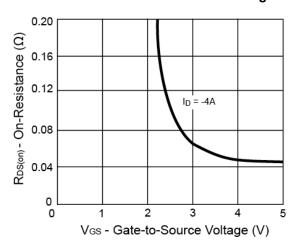


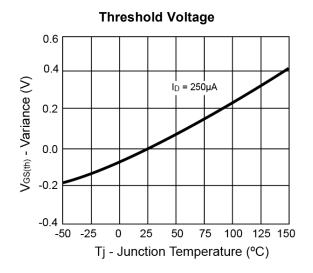




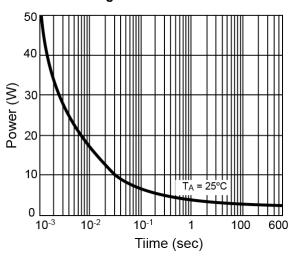
## Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

## On-Resistance vs. Gate-Source Voltage

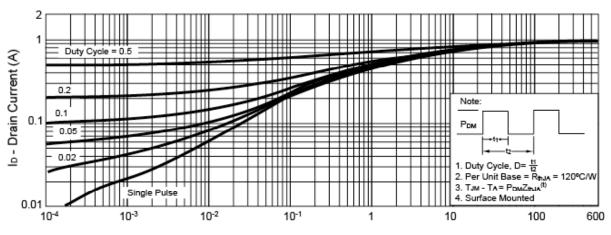




## Single Pulse Power



## Normalized Thermal Transient Impedance, Junction-to-Ambient



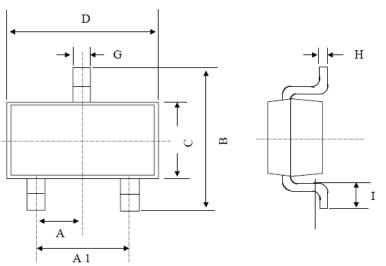
Square Wave Pulse Duration (sec)



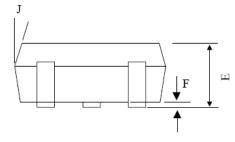




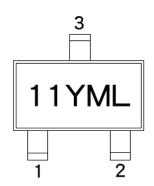
# **SOT-23 Mechanical Drawing**



SOT-23 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	0.95	0.95 BSC		BSC	
A1	1.9 I	BSC	0.074 BSC		
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
Е	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Н	0.10	0.20	0.004	0.008	
Ī	0.30	0.60	0.012	0.024	
J	5°	10°	5°	10°	



# **Marking Diagram**



11 = Device Code

Y = Year Code

**M** = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

5/6

L = Lot Code

Version: A07



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